

GSM3009S

30V N-Channel Enhancement Mode MOSFET

Product Description

GSM3009S, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

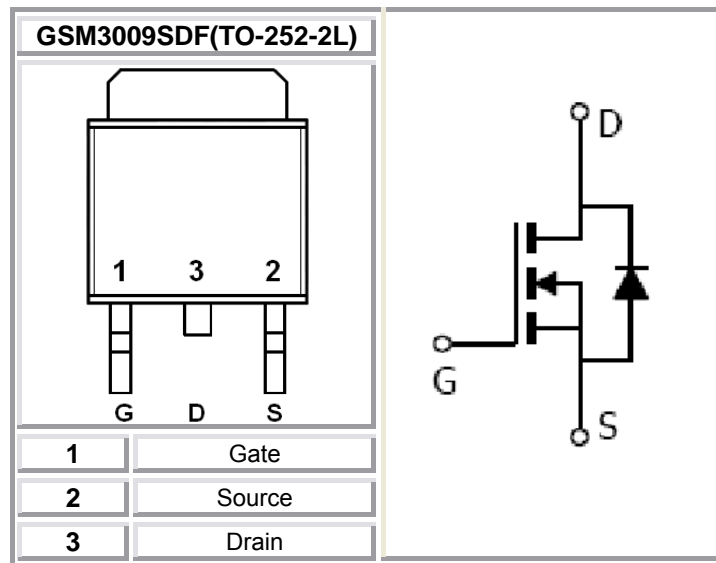
Features

- 30V/35A, $R_{DS(ON)}=8.5m\Omega@V_{GS}=10V$
- 30V/20A, $R_{DS(ON)}=11.5m\Omega@V_{GS}=4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- TO-252-2L package design

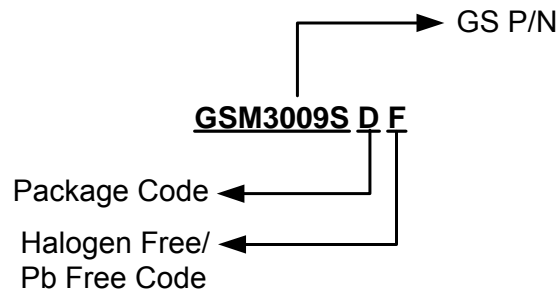
Applications

- Buck Converter-High Side / Low Side
- Synchronous Rectifier-Secondary Rectifier

Packages & Pin Assignments

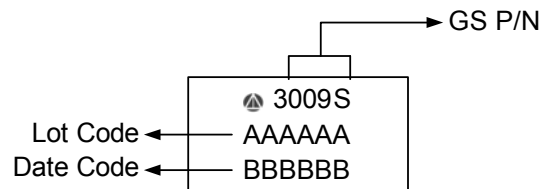


Ordering Information



Part Number	Package	Quantity Reel
GSM3009SDF	TO-252-2L	2500 PCS

Marking Information



Absolute Maximum Ratings

($T_A=25^\circ\text{C}$ unless otherwise noted)

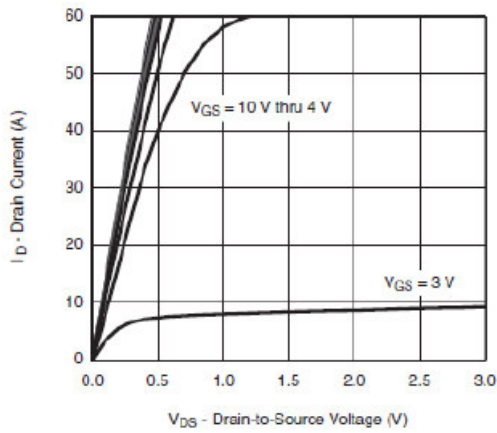
Symbol	Parameter	Typical	Unit	
V_{DSS}	Drain-Source Voltage	30	V	
V_{GSS}	Gate –Source Voltage	± 20	V	
I_D	Continuous Drain Current($T_J=150^\circ\text{C}$)	$T_A=25^\circ\text{C}$	60	A
		$T_A=70^\circ\text{C}$	42	
I_{DM}	Pulsed Drain Current	160	A	
I_S	Continuous Source Current(Diode Conduction)	9.0	A	
P_D	Power Dissipation	$T_A=25^\circ\text{C}$	40	W
		$T_A=70^\circ\text{C}$	15	
T_J	Operating Junction Temperature	150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-55/150	$^\circ\text{C}$	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62.5	$^\circ\text{C}/\text{W}$	

Electrical Characteristics

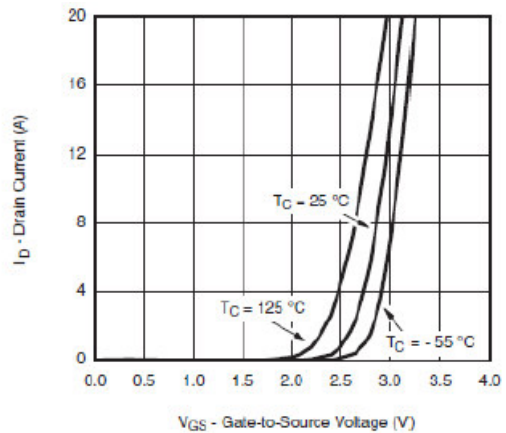
($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		2.0	
I_{GSS}	Gate Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24V, V_{GS}=0V$			1	uA
		$V_{DS}=24V, V_{GS}=0V, T_J=85^\circ\text{C}$			10	
$I_{D(on)}$	On-State Drain Current	$V_{DS}\geq 5V, V_{GS}=10V$	15			A
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V, I_D=35A$		6	8.5	m Ω
		$V_{GS}=4.5V, I_D=20A$		8	11.5	
g_{fs}	Forward Transconductance	$V_{DS}=15V, I_D=10A$		32		S
V_{SD}	Diode Forward Voltage	$I_S=30A, V_{GS}=0V$		0.8	1.3	V
Dynamic						
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$		1350		pF
C_{oss}	Output Capacitance			210		
C_{rss}	Reverse Transfer Capacitance			95		
Q_g	Total Gate Charge	$V_{DS}=15V, V_{GS}=4.5V, I_D=15A$		8	13	nC
Q_{gs}	Gate-Source Charge			3.7		
Q_{gd}	Gate-Drain Charge			2.7		
$t_{d(on)}$	Turn-On Time	$V_{DD}=15V, R_L=1.5\Omega, I_D=10A, V_{GEN}=10V, R_G=1\Omega$		10	15	ns
t_r				10	15	
$t_{d(off)}$	Turn-Off Time			25	35	
t_f				10	15	

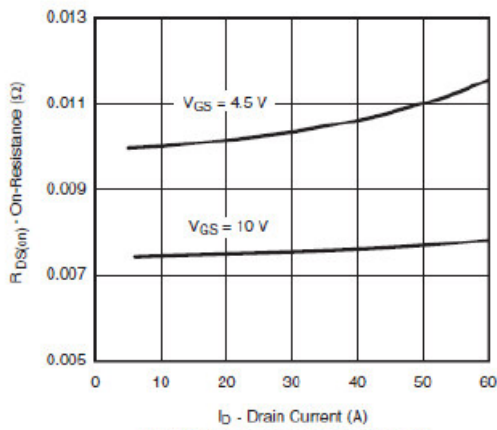
Typical Performance Characteristics



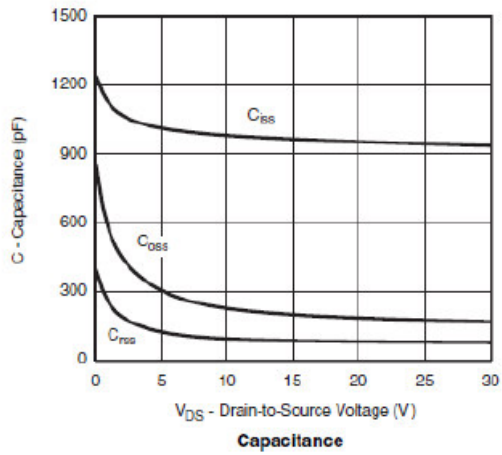
Output Characteristics



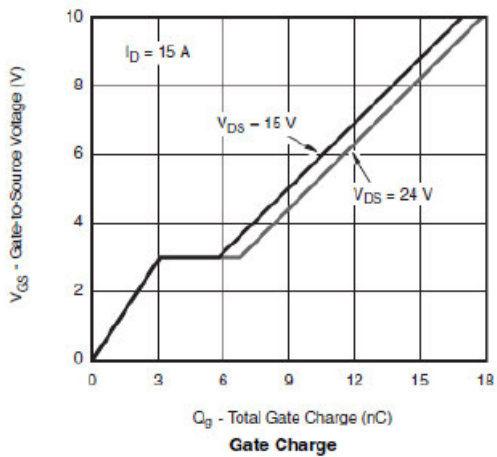
Transfer Characteristics



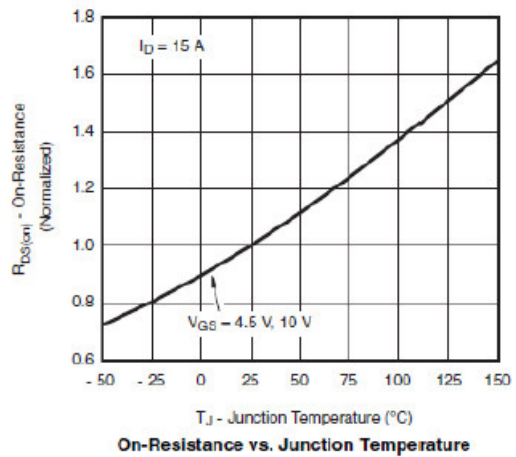
On-Resistance vs. Drain Current



Capacitance

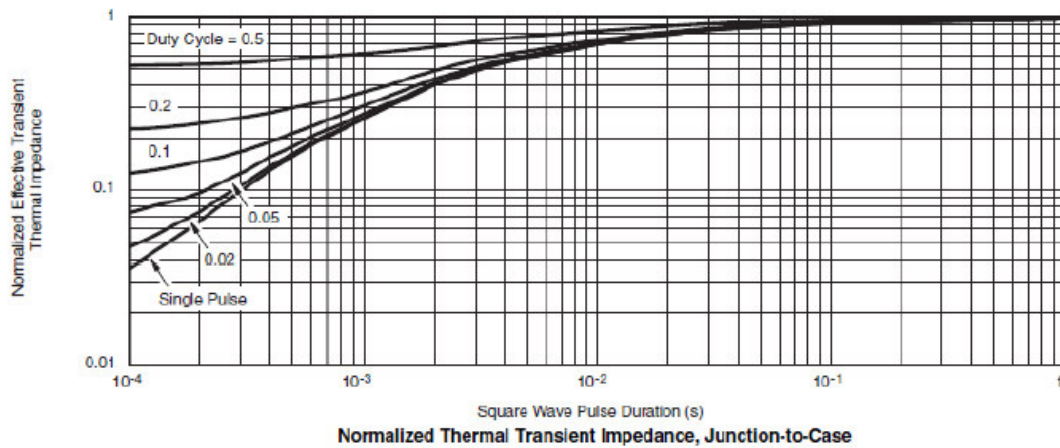
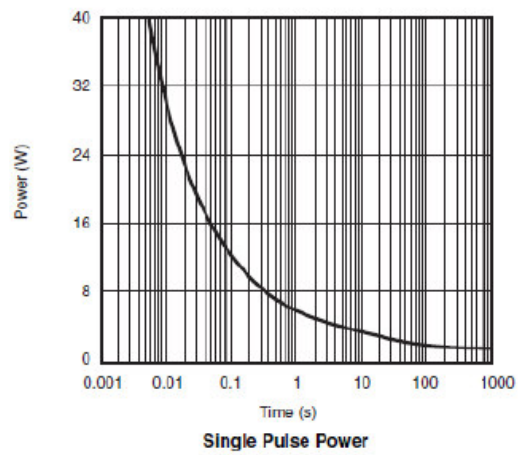
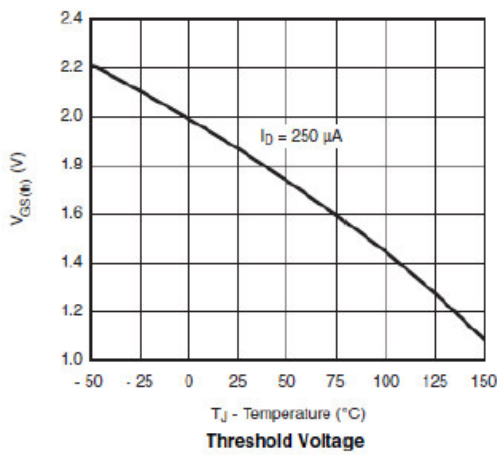
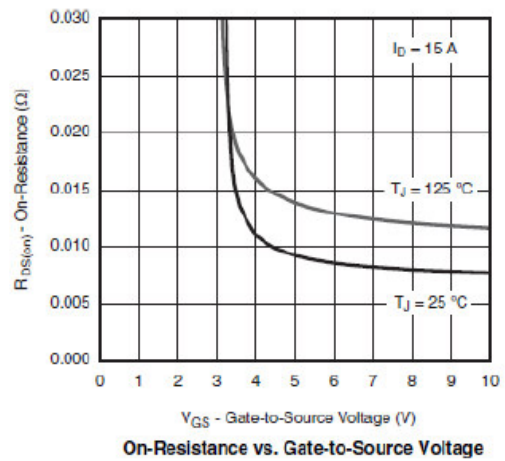
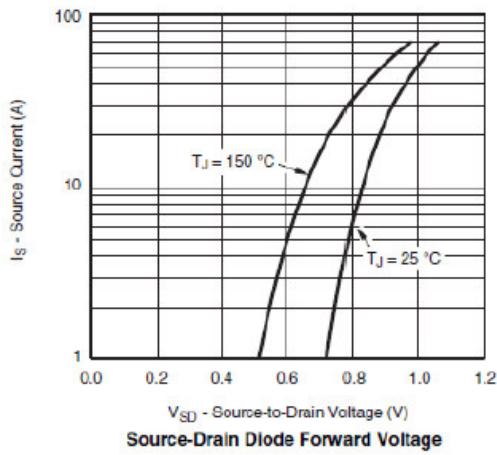


Gate Charge



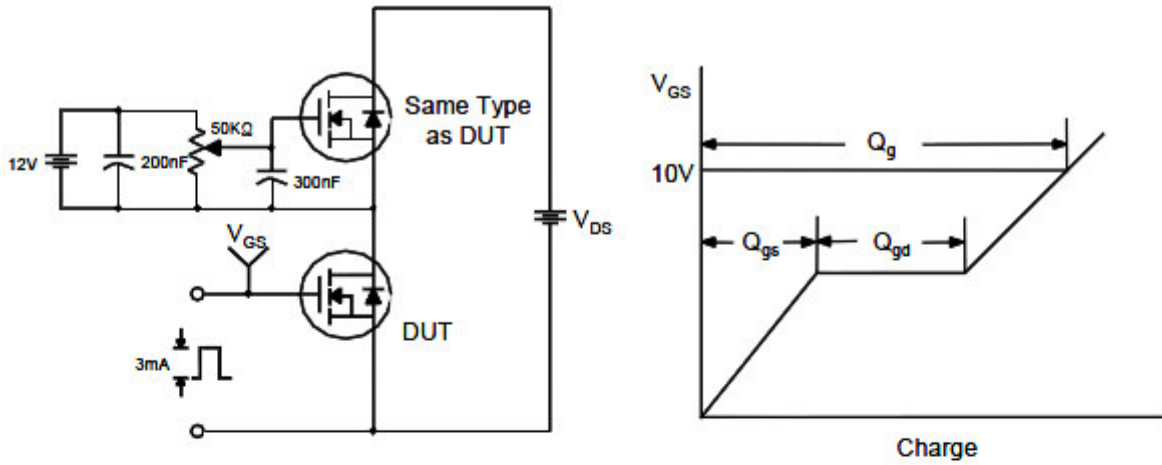
On-Resistance vs. Junction Temperature

Typical Performance Characteristics (continue)

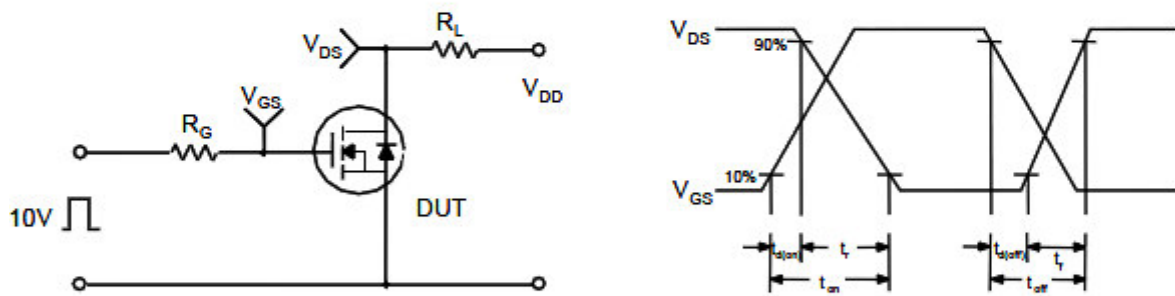


Typical Characteristics

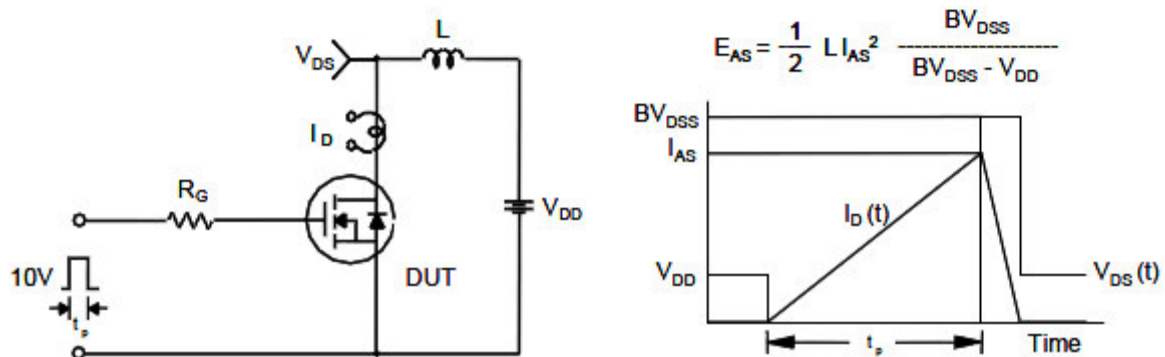
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

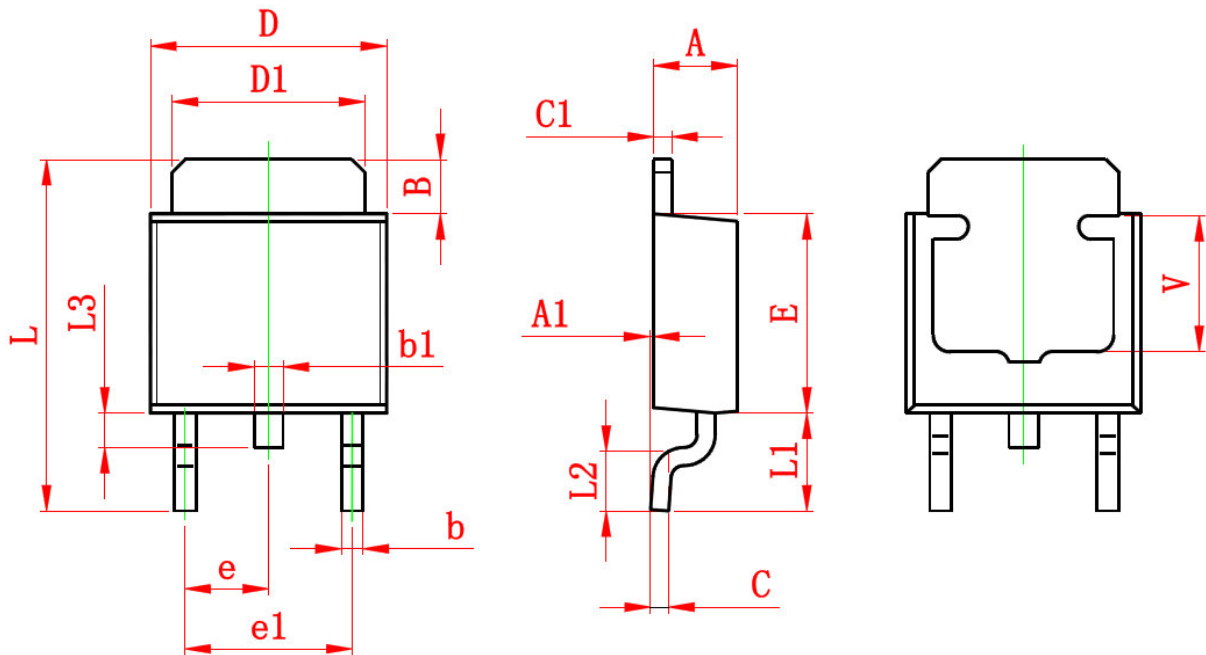


Unclamped Inductive Switching Test Circuit & Waveforms



Package Dimension

TO-252-2L PLASTIC PACKAGE







Dimensions





SYMBOL	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP		0.091 TYP	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF		0.150 REF	



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CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

Wu-Xi Branch	
	No.21 Changjiang Rd., WND, Wuxi, Jiangsu, China (INFO. &. TECH. Science Park Building A 210 Room)
	86-510-85217051
	86-510-85211238
	sales_cn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587